

# **HSM88WK**

## Silicon Schottky Barrier Diode for Detector and Mixer

REJ03G0138-0700Z

(Previous: ADE-208-049F)

Rev.7.00

Nov.06.2003

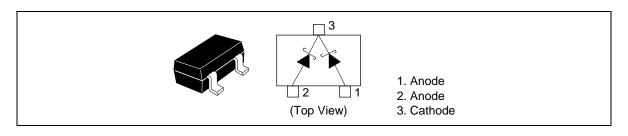
#### **Features**

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

Type No.	Laser Mark	Package Code	
HSM88WK	C4	MPAK	

## **Pin Arrangement**



#### HSM88WK

## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit
Reverse voltage	$V_{R}$	10	V
Average rectified current	l <sub>0</sub> * <sup>1</sup>	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: 1. Per one device

## **Electrical Characteristics** \*1

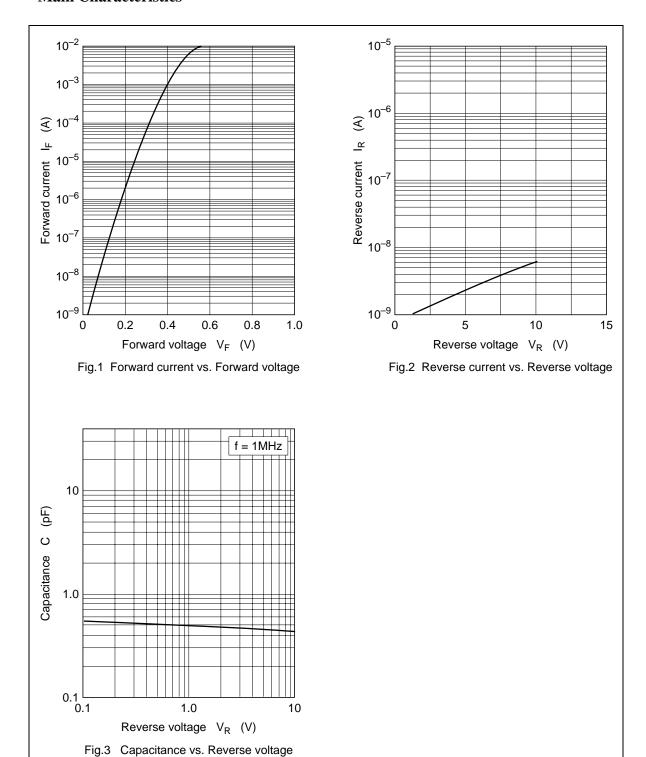
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	0.35	_	0.42	V	$I_F = 1 \text{ mA}$
	V <sub>F2</sub>	0.50	_	0.58	='	I <sub>F</sub> = 10 mA
Reverse current	I <sub>R1</sub>	_	_	0.2	μΑ	V <sub>R</sub> = 2 V
	I <sub>R2</sub>	_	_	10	='	V <sub>R</sub> = 10 V
Capacitance	С	_	_	0.85	рF	V <sub>R</sub> = 0 V, f = 1 MHz
Capacitance deviation	ΔC	_	_	0.10	рF	$V_R = 0 V, f = 1 MHz$
Forward voltage deviation	$\Delta V_{F}$	_	_	10	mV	I <sub>F</sub> = 10 mA
ESD-Capability *2	_	30	_	_	V	$C = 200 \text{ pF}, R = 0 \Omega$ , Both forward and reverse direction 1 pulse.

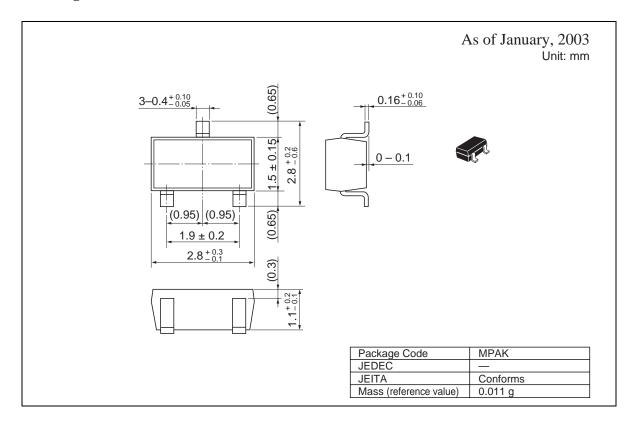
Notes: 1. Per one device

2. Failure criterion ;  $I_R \geq 0.4~\mu\text{A}$  at  $V_R$  = 2 V

#### **Main Characteristics**



## **Package Dimensions**



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Renesas Technology Singapore Pte. Ltd.
1, Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

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